

In the Claims:

Please cancel claims 10-15, without prejudice.

1. (Original) A thin film transistor substrate, comprising:

a transparent insulating substrate;

a first thin film transistor that is formed on the transparent insulating substrate;

and

a second thin film transistor that is formed on the transparent insulating substrate, the second thin film transistor having a characteristic that differs from a characteristic of the first thin film transistor;

wherein an active layer of the first thin film transistor has a thickness greater than or equal to 50 nm, and an average crystal grain diameter greater than or equal to 1 μm ;

and

an active layer of the second thin film transistor has a thickness less than or equal to 60 nm, and an average crystal grain diameter of less than 1 μm .

2. (Original) The thin film transistor substrate as claimed in claim 1, wherein the active layer of the first thin film transistor corresponds to polycrystalline silicon that is laterally crystallized through selective irradiation of a continuous wave laser.

3. (Original) The thin film transistor substrate as claimed in claim 1, wherein the active layer of the second thin film transistor corresponds to polycrystalline silicon that is crystallized through irradiation of an excimer laser.

4. (Original) The thin film transistor substrate as claimed in claim 1, wherein a gate insulating film of the first thin film transistor is arranged to be thinner than a gate insulating film of the second thin film transistor.

5. (Original) The thin film transistor substrate as claimed in claim 4, wherein the gate insulating film of the second thin film transistor is arranged to have a film thickness greater than equal to 80 nm.

6. (Original) A thin film transistor substrate, comprising:
a transparent insulating substrate;
a first thin film transistor that is formed on the transparent insulating substrate;
and
a second thin film transistor that is formed on the transparent insulating substrate, the second thin film transistor having a characteristic that differs from a characteristic of the first thin film transistor;

wherein an active layer of the first thin film transistor has an average crystal grain diameter greater than or equal to 1 μm , and an active layer of the second thin film transistor has an average crystal grain diameter less than 1 μm ; and

a gate insulating film of the first thin film transistor is arranged to be thinner than a gate insulating film of the second thin film transistor.

7. (Original) The thin film transistor substrate as claimed in claim 6, wherein the active layer of the first thin film transistor corresponds to polycrystalline silicon that is laterally crystallized through selective irradiation of a continuous wave laser.

8. (Original) The thin film transistor substrate as claimed in claim 6, wherein the active layer of the second thin film transistor corresponds to polycrystalline silicon that is crystallized through irradiation of an excimer laser.

9. (Original) The thin film transistor substrate as claimed in claim 6, wherein the gate insulating film of the second thin film transistor is arranged to have a film greater than or equal to 80 nm.

10-15. (Cancelled)

Respectfully submitted,

GREER, BURNS & CRAIN, LTD.

By

A handwritten signature in black ink, appearing to read 'PGB', with a long horizontal flourish extending to the right.

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